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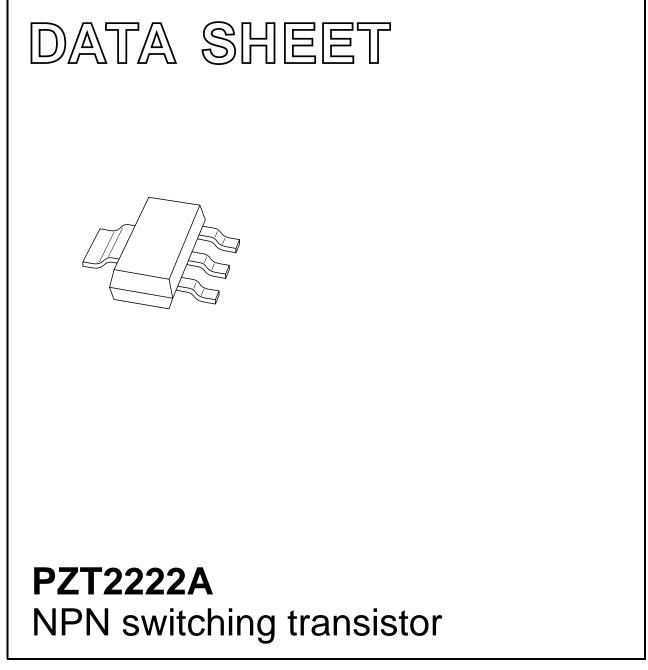
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 Jun 02 1999 Apr 14



PZT2222A

NPN switching transistor

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

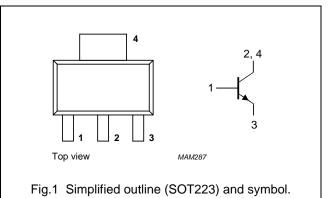
• Switching and linear amplification.

DESCRIPTION

NPN switching transistor in a SOT223 plastic package. PNP complement: PZT2907A.

PINNING

PIN	DESCRIPTION	
1	base	
2, 4	collector	
3	emitter	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	75	V
V _{CEO}	collector-emitter voltage	open base	-	40	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current (DC)		-	600	mA
I _{CM}	peak collector current		-	800	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation $T_{amb} \le 25 \text{ °C}$; note 1		_	1.15	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	109	K/W
R _{th j-s}	thermal resistance from junction to soldering point		28	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

CHARACTERISTICS

 T_j = 25 °C unless otherwise specified.

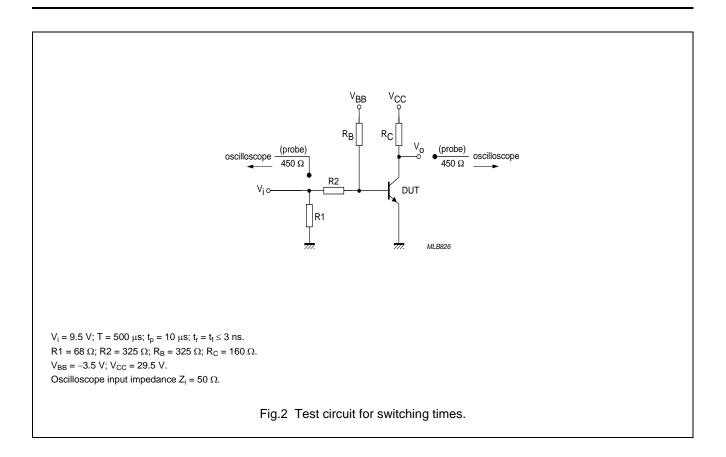
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 60 V	_	10	nA
		$I_E = 0; V_{CB} = 60 V; T_{amb} = 125 °C$	-	10	μA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	-	10	nA
h _{FE}	DC current gain	I _C = 0.1 mA; V _{CE} = 10 V	35	_	
		I _C = 1 mA; V _{CE} = 10 V	50	-	
		I _C = 10 mA; V _{CE} = 10 V	75	_	
1		$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V};$ $T_{amb} = -55 \text{ °C}$	35	-	
		I _C = 150 mA; V _{CE} = 1 V; note 1	50	_	
		I _C = 150 mA; V _{CE} = 10 V; note 1	100	300	
		I _C = 500 mA; V _{CE} = 10 V; note 1	40	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA	-	300	mV
		I _C = 500 mA; I _B = 50 mA	-	1	V
V _{BEsat}	base-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA	0.6	1.2	V
		I _C = 500 mA; I _B = 50 mA	-	2	V
Cc	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz	-	8	pF
Ce	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = 500 \text{ mV}; f = 1 \text{ MHz}$	-	25	pF
f _T	transition frequency	I _C = 20 mA; V _{CE} = 20 V; f = 100 MHz	300	-	MHz
Switching	times (between 10% and 90% levels); (see Fig.2)			•
t _{on}	turn-on time	I _{Con} = 150 mA; I _{Bon} = 15 mA;	-	35	ns
t _d	delay time	$I_{Boff} = -15 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	_	10	ns
t _r	rise time	1	_	25	ns
t _{off}	turn-off time	1	-	250	ns
ts	storage time	1	-	200	ns
t _f	fall time	1	-	60	ns

Note

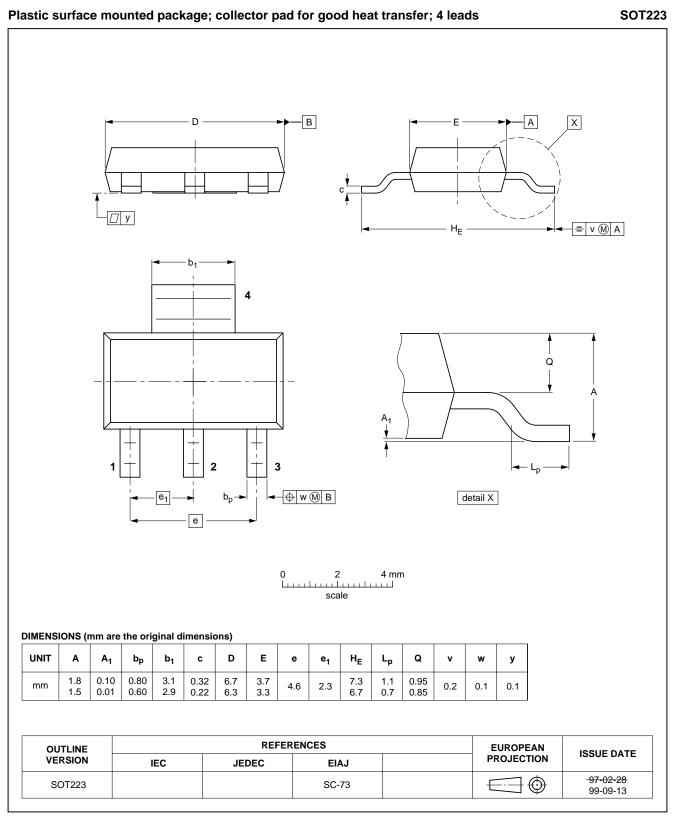
1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

1999 Apr 14

PZT2222A



PACKAGE OUTLINE



Downloaded from Arrow.com.

PZT2222A

PZT2222A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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